

DMN53D0L-13 Datasheet



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DiGi Electronics Part Number	DMN53D0L-13-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN53D0L-13
Description	MOSFET N-CH 50V 500MA SOT23
Detailed Description	N-Channel 50 V 500mA (Ta) 370mW (Ta) Surface Mount SOT-23-3



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Purchase and inquiry

Manufacturer Product Number:

DMN53D0L-13

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

50 V

Drive Voltage (Max Rds On, Min Rds On):

2.5V, 10V

Vgs(th) (Max) @ Id:

1.5V @ 250 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-23-3

Base Product Number:

DMN53

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

500mA (Ta)

Rds On (Max) @ Id, Vgs:

1.6Ohm @ 500mA, 10V

Gate Charge (Qg) (Max) @ Vgs:

0.6 nC @ 4.5 V

Input Capacitance (Ciss) (Max) @ Vds:

46 pF @ 25 V

Power Dissipation (Max):

370mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-236-3, SC-59, SOT-23-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN53D0L

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
50V	1.6Ω @ $V_{GS} = 10V$	500mA
	2.5Ω @ $V_{GS} = 4.5V$	200mA

Features and Benefits

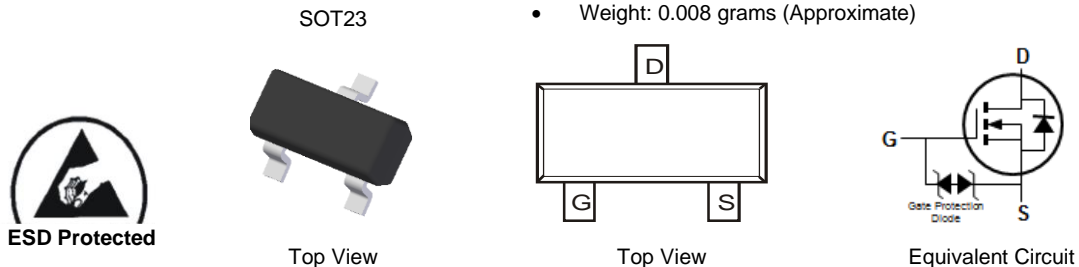
- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet ([DMN53D0LQ](#))**

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

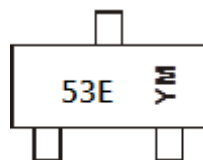


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN53D0L-7	SOT23	3000	Tape & Reel
DMN53D0L-13	SOT23	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



53E = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} or \underline{Y} = Year (ex: L = 2024)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	B	-	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMN53D0L

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	370	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	344	°C/W
Total Power Dissipation (Note 5)	P _D	540	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	236	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.8	—	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	1.6	Ω	V _{GS} = 10V, I _D = 500mA
		—	—	2.5		V _{GS} = 4.5V, I _D = 200mA
		—	—	4.5		V _{GS} = 2.5V, I _D = 100mA
Source-Drain Diode Forward Voltage	V _{SD}	—	—	1.4	V	V _{GS} = 0V, I _S = 500mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	46	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	5.3	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	4.0	—	pF	
Total Gate Charge	Q _g	—	0.6	—	nC	V _{GS} = 4.5V, V _{DS} = 10V I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(on)}	—	2.7	—	ns	V _{DD} = 30V, V _{GS} = 10V R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	2.5	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	19	—	ns	
Turn-Off Fall Time	t _f	—	11	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



DMN53D0L

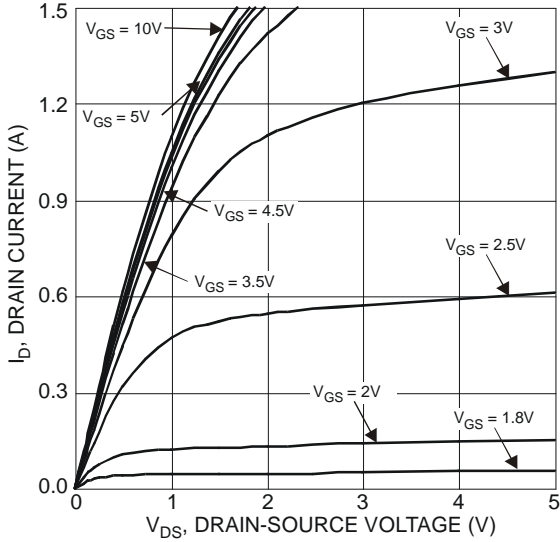


Figure 1 Typical Output Characteristics

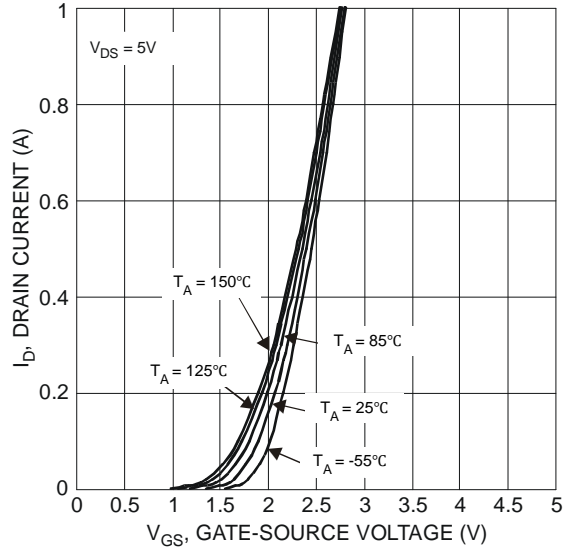


Figure 2 Typical Transfer Characteristics

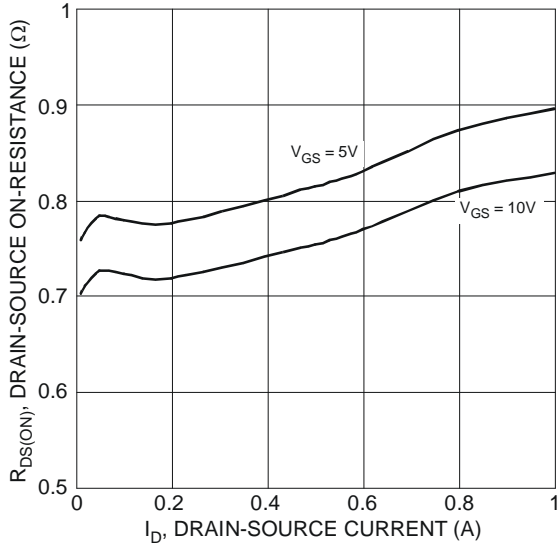


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

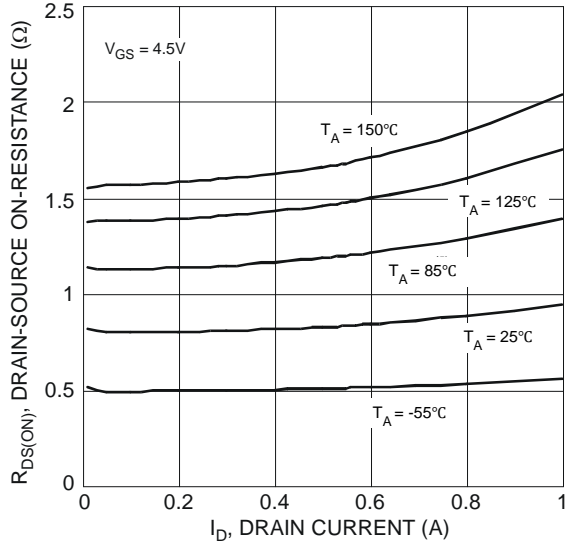


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

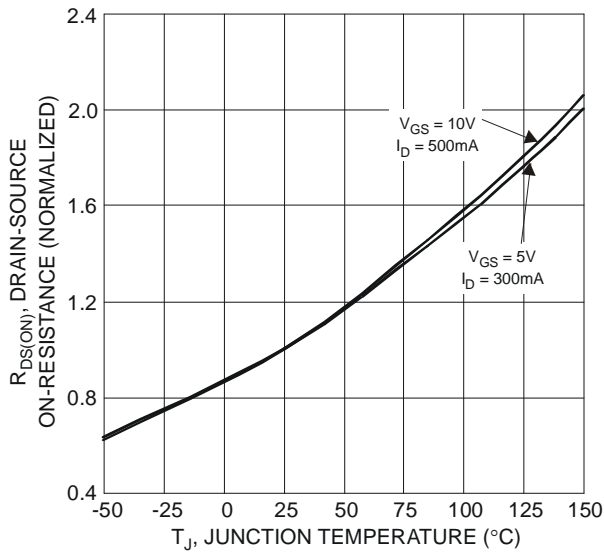


Figure 5 On-Resistance Variation with Temperature

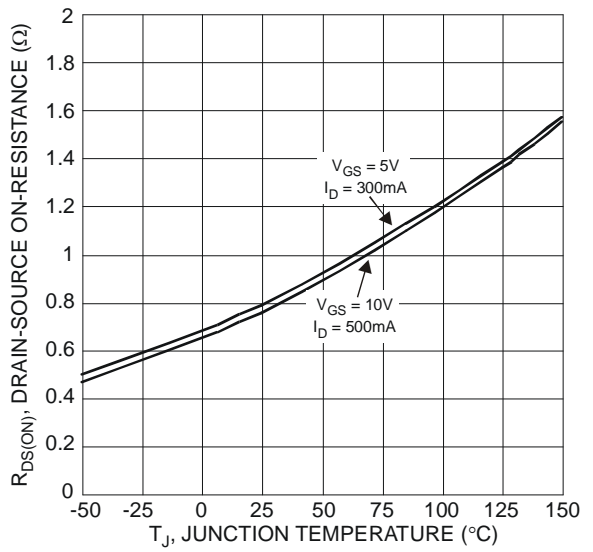


Figure 6 On-Resistance Variation with Temperature



DMN53D0L

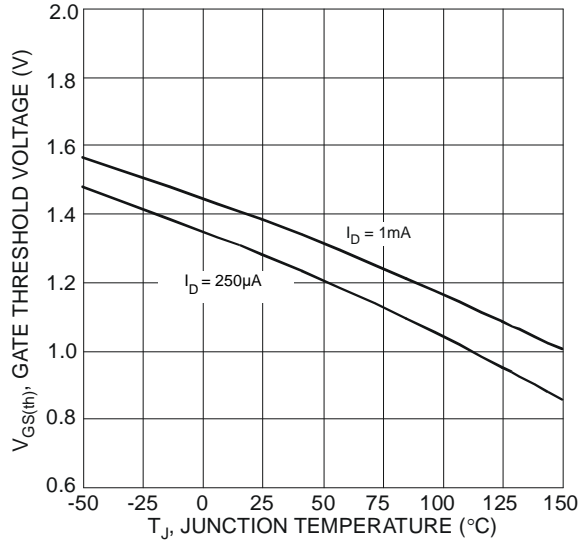


Figure 7 Gate Threshold Variation vs. Junction Temperature

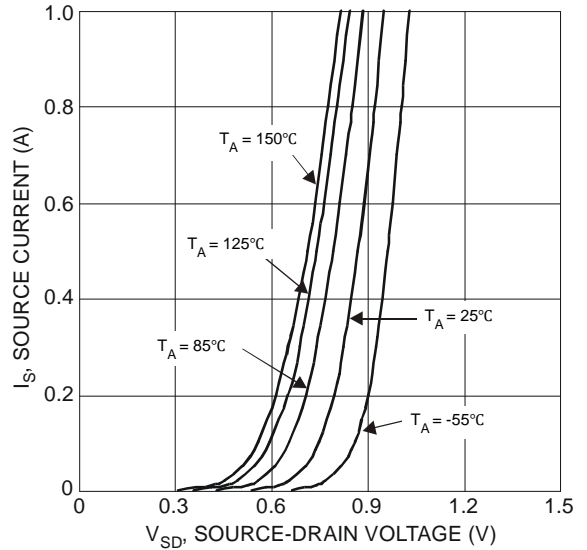


Figure 8 Diode Forward Voltage vs. Current

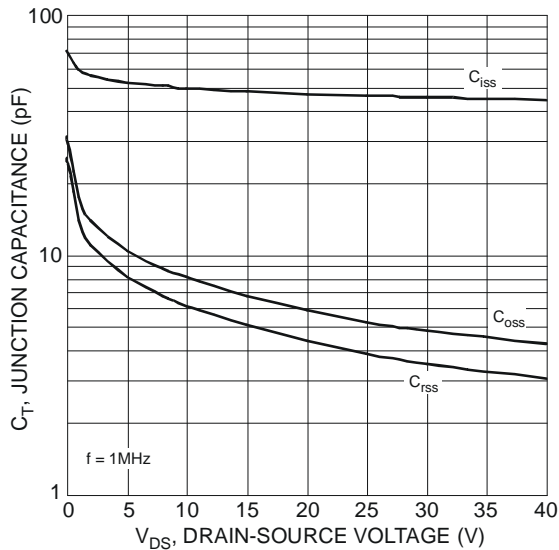


Figure 9 Typical Junction Capacitance

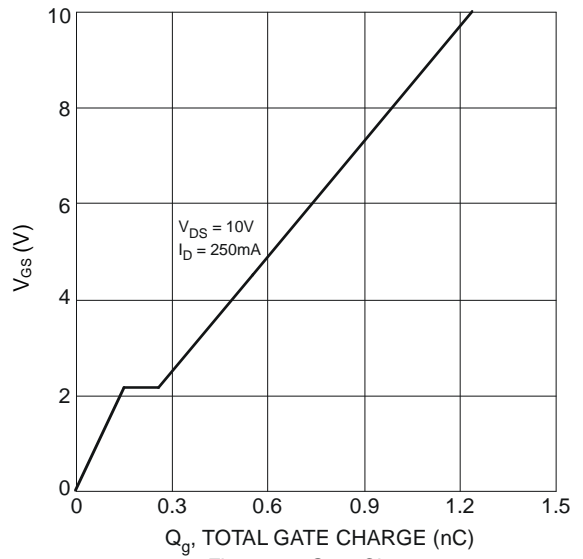
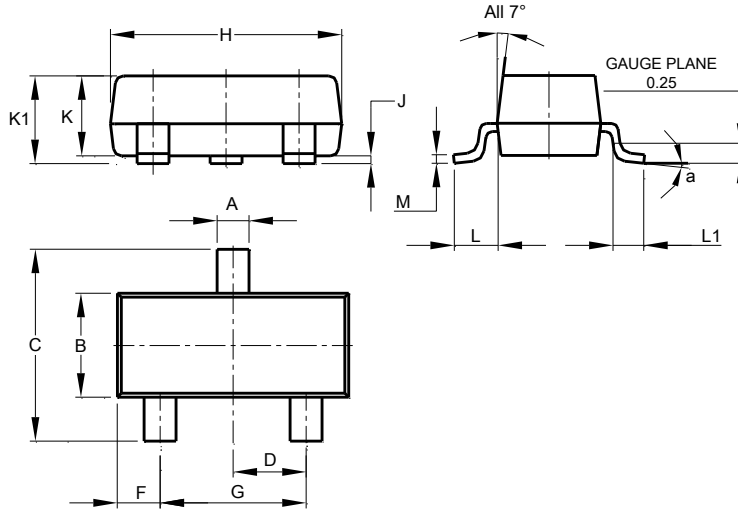


Figure 10 Gate Charge

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

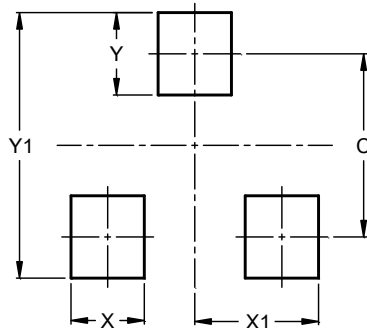


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.10	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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